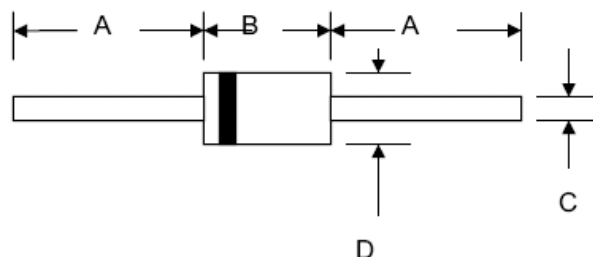


Technical Data
Data Sheet N0445, Rev. -

Green Products

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

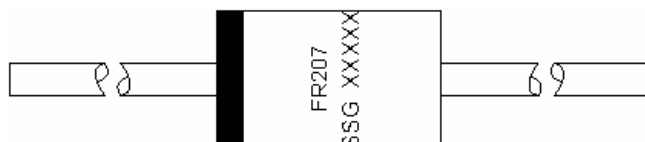


Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.40 grams (approx.)
- Mounting Position: Any
- Marking: Type Number

DO-15					
Dim	Min	Max	Min	Max	
A	25.4	—	1.000	—	
B	5.50	7.62	0.217	0.300	
C	0.71	0.864	0.028	0.034	
D	2.60	3.60	0.102	0.142	
	In mm		In inch		

Marking Diagram:



Where XXXXX is YYWWL

FR207 = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
FR201-FR207	DO-15 (Pb-Free)	3000pcs / tape

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

Characteristic	Symbol	FR201	FR202	FR203	FR204	FR205	FR206	FR207	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T _A = 55°C	I _O	2.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	60							A
Forward Voltage @I _F = 2.0A	V _{FM}	1.2							V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	5.0 100							μA
Reverse Recovery Time (Note 2)	t _{rr}	150				250	500		nS
Typical Junction Capacitance (Note 3)	C _j	30							pF
Operating Temperature Range	T _j	-65 to +125							°C
Storage Temperature Range	T _{STG}	-65 to +150							°C

***Glass passivated forms are available upon request**

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured with I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A. See figure 5.

3. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

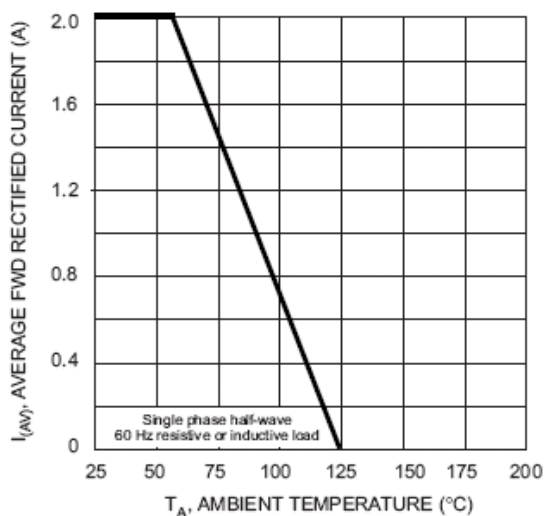


Fig. 1 Forward Derating Curve

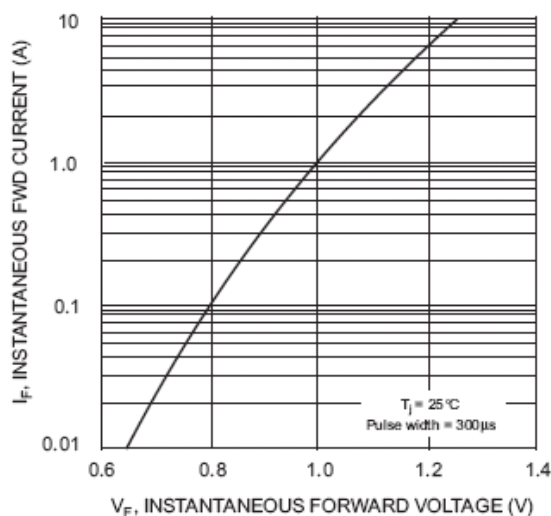


Fig. 2 Typical Forward Characteristics

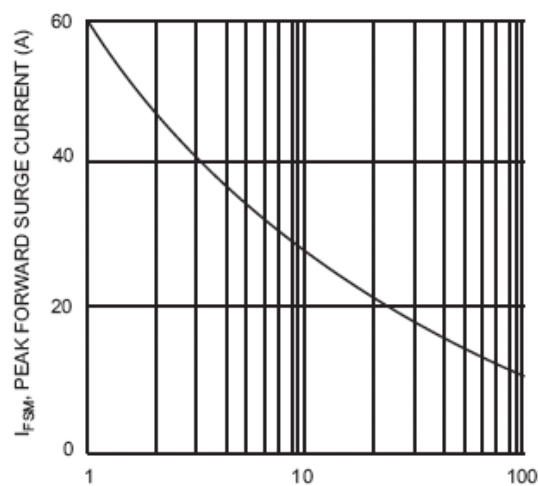


Fig. 3 Peak Forward Surge Current

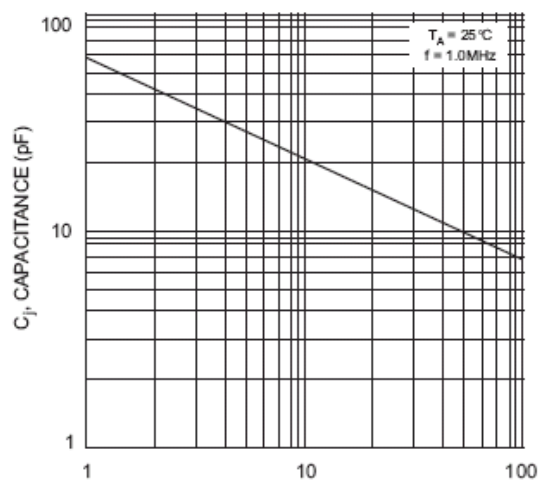
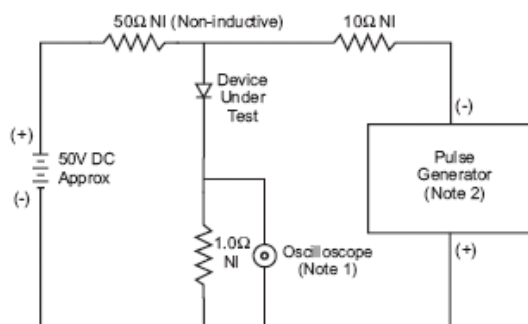
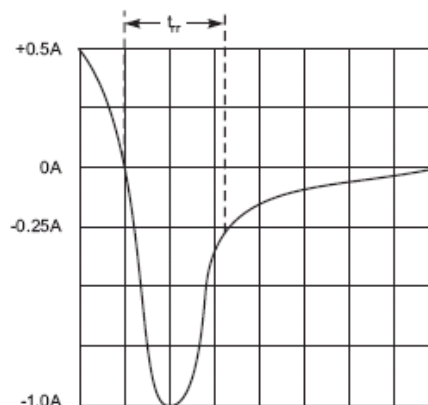


Fig. 4 Typical Junction Capacitance



Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.
2. Rise Time = 10ns max. Input Impedance = 50Ω.



Set time base for 5/10ns/cm

Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

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